

Supplementary Information

Role of the electron transport layer in dictating the nanoscale heterogeneity in all-inorganic perovskite absorbers – correlating the optoelectronic and crystallographic properties

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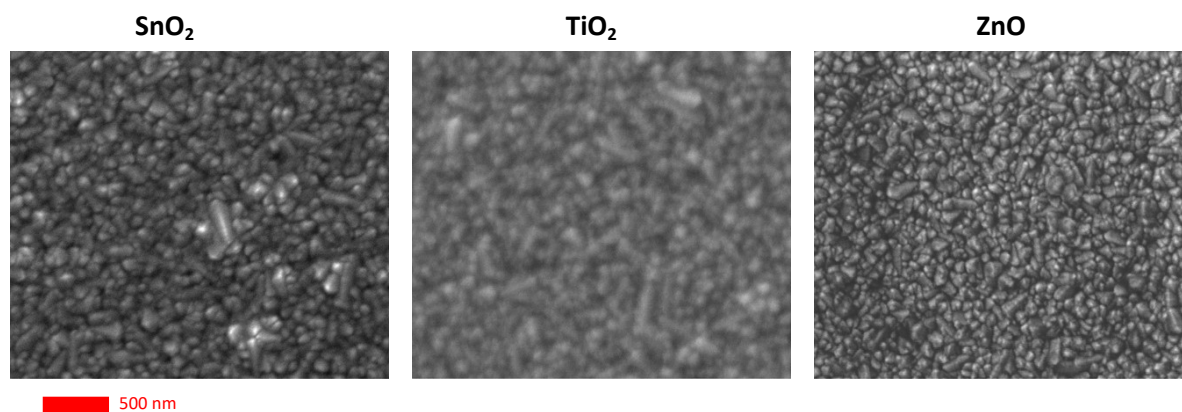


Figure S1 – Topographic SEM images of the electron transport layers deposited on FTO coated glass substrates (TEC 15). F

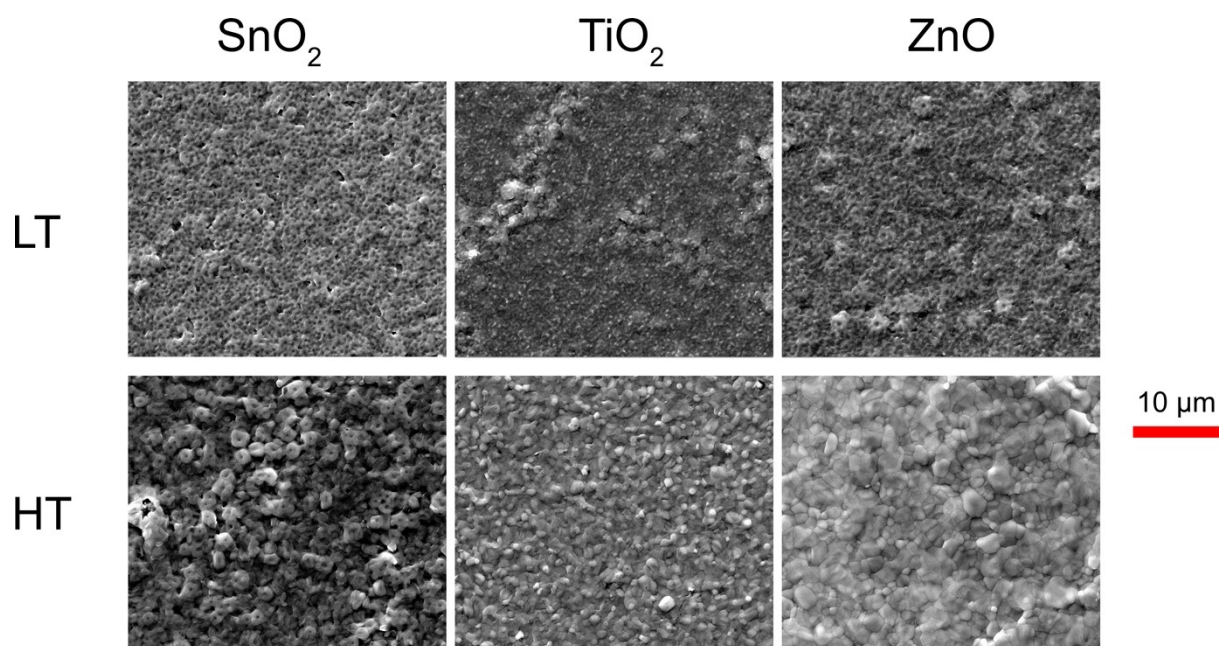


Figure S2 – Topography of CsPbI₂Br films grown on the three ETL's (SnO₂, TiO₂ and ZnO) at high (160 °C) and low (280 °C) temperatures.

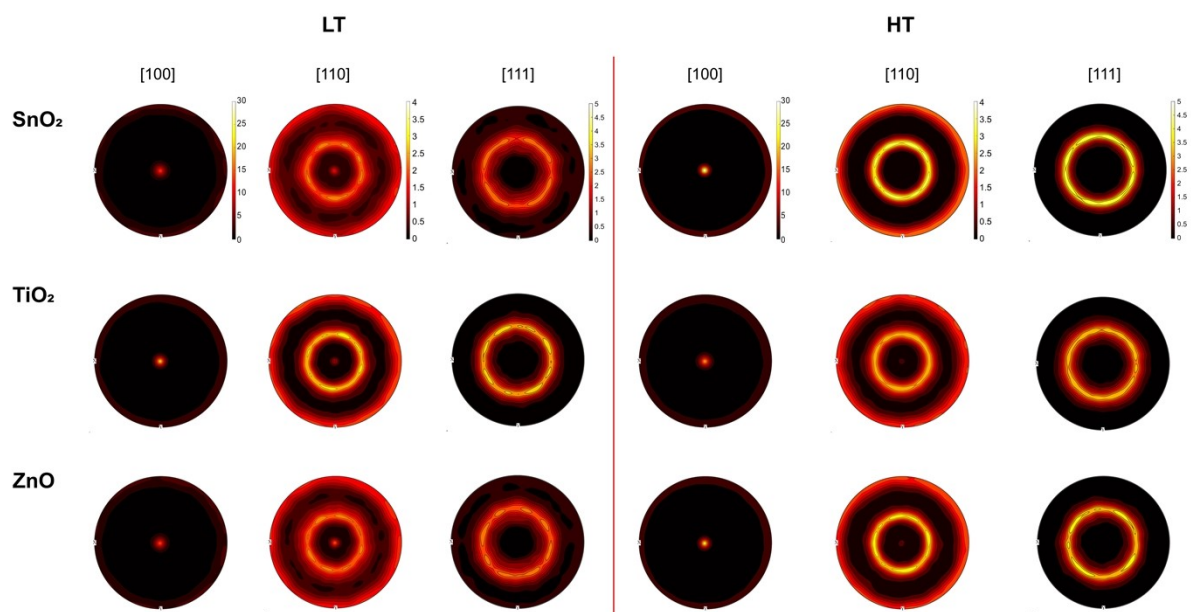


Figure S3 – Full pole figures for CsPbI₂Br films grown on the ETLs at high and low temperature, including the [111].

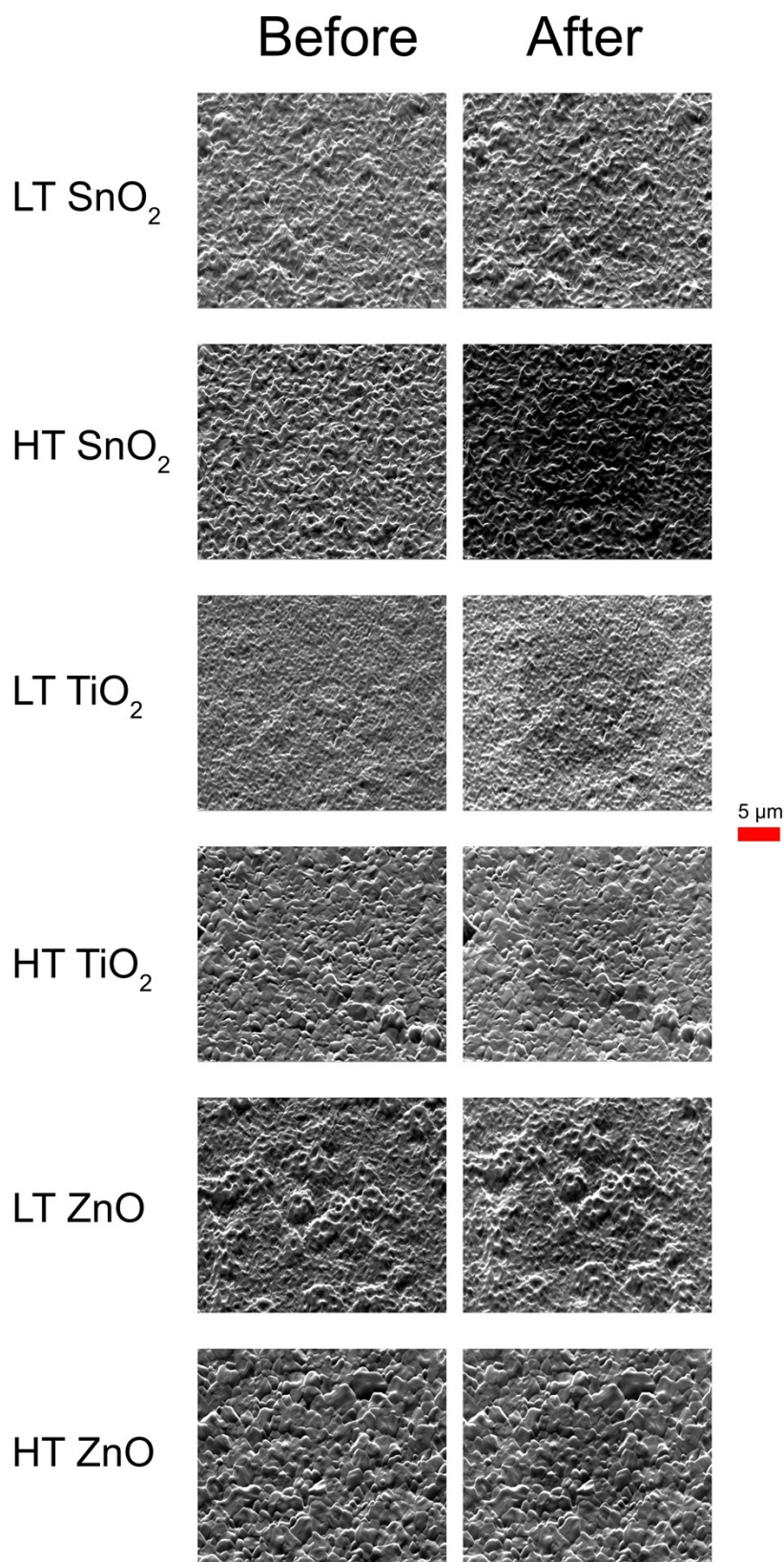


Figure S4 – Secondary Electron images of regions of CsPbI₂Br films on the different ETLs before and after EBSD mapping.

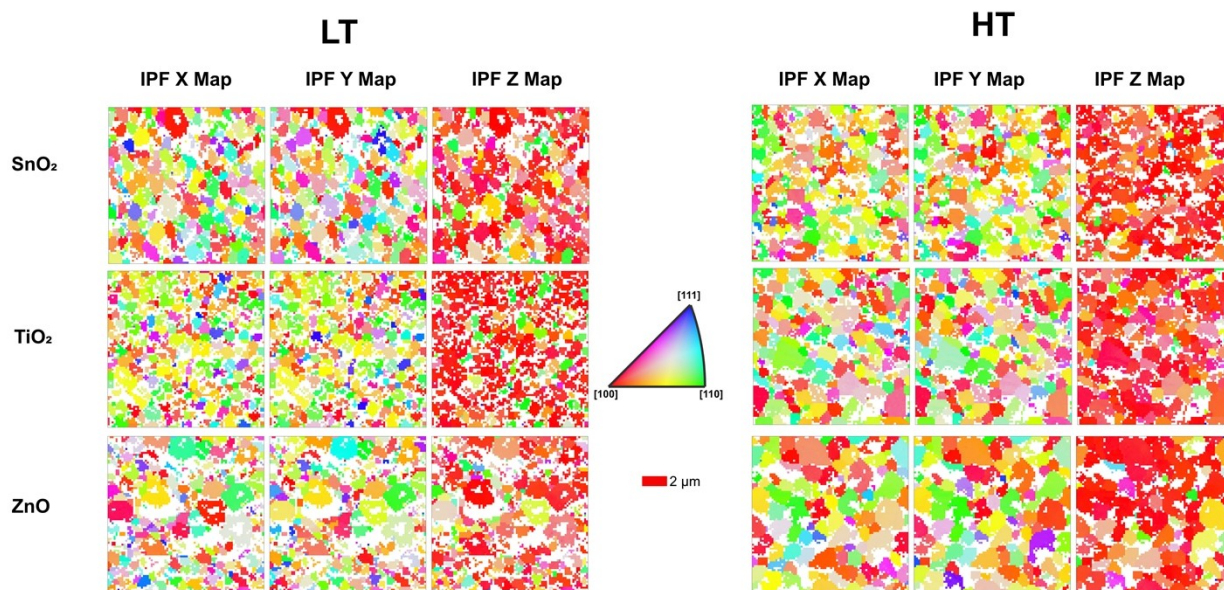


Figure S5 – IPF maps for the samples, including the X maps.

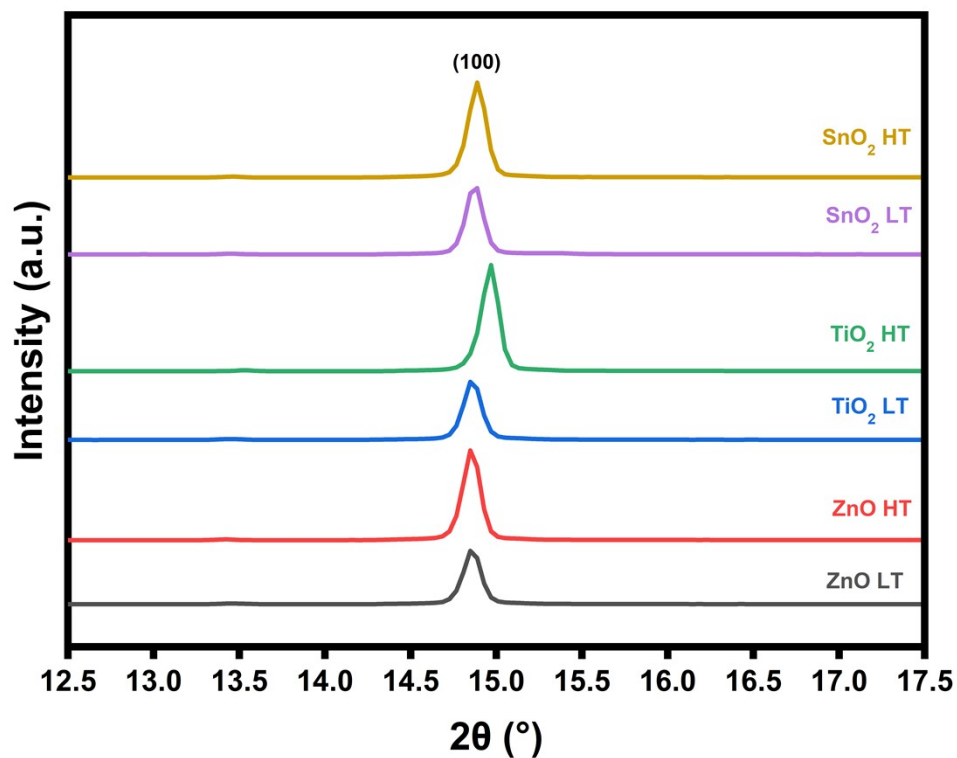


Figure S6 – XRD showing magnified (100) peak, with shifts similar to the (200) peak for the perovskite samples grown on SnO₂, TiO₂ and ZnO at high and low temperatures.